

SEMITOP[®] 3

IGBT Module

SK50GH065F

Target Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonding aluminium oxide ceramic (DBC)
- Ultrafast NPT IGBT
- Turbo FWDiodes
- Low treshold voltage
- Low tail current with low temperature dependence

Typical Applications*

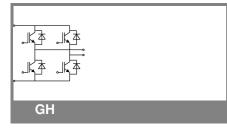
- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS

Remarks

• V_F = chip level value

Absolut	e Maximum Ratings	Τ _s	= 25 °C, unless otherwise	e specified
Symbol	Conditions		Values	Units
IGBT				
V _{CES}	T _j = 25 °C		600	V
I _C	T _j = 125 °C	T _s = 25 °C	54	А
		T _s = 80 °C	40	А
I _{CRM}	I _{CRM} = 2 x I _{Cnom}		100	А
V _{GES}			± 20	V
t _{psc}	$V_{CC} = 300 \text{ V}; \text{ V}_{GE} \le 20 \text{ V}; \\ \text{V}_{CES} < 600 \text{ V}$	T _j = 125 °C	10	μs
Inverse	Diode			
I _F	T _j = 150 °C	T _s = 25 °C	82	А
		T _s = 80 °C	50	А
I _{FRM}	I _{FRM} = 2 x I _{Fnom}		120	А
Module				
I _{t(RMS)}				А
T _{vj}			-40 +150	°C
T _{stg}			-40 +125	°C
V _{isol}	AC, 1 min.		2500	V

Characte	ristics	T _s =	25 °C, ur	iless oth	erwise sp	pecified
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	$V_{GE} = V_{CE}, I_C = 0.7 \text{ mA}$		3	4	5	V
I _{CES}	V_{GE} = 600 V, V_{CE} = V_{CES}	T _j = 25 °C			0,0022	mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 20 V	T _j = 25 °C			120	nA
V _{CE0}		T _i = 25 °C		1,2	1,3	V
		T _j = 125 °C		1,1	0,9	V
r _{CE}	V _{GE} = 15 V	T _i = 25°C			12	mΩ
		T _j = 125°C			22	mΩ
V _{CE(sat)}	I _{Cnom} = 60 A, V _{GE} = 15 V	T _j = 25°C _{chiplev.}		2	2,5	V
		T _j = 125°C _{chiplev.}		2,2	2,7	V
Cies				3,2		nF
C _{oes}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		0,3		nF
C _{res}				0,18		nF
t _{d(on)}						ns
tr	R _{Gon} = 15 Ω	V _{CC} = 300V				ns
E _{on}	di/dt = 1200 A/µs	I _C = 60A		1,07		mJ
t _{d(off)}	R_{Goff} = 15 Ω	T _j = 125 °C				ns
t _f	di/dt = 1200 A/µs	V _{GE} =±15V				ns
E _{off}				1,76		mJ
R _{th(j-s)}	per IGBT				0,85	K/W





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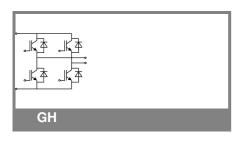
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Characteristics								
Symbol	Conditions		min.	typ.	max.	Units		
Inverse Diode								
$V_F = V_{EC}$	I _{Fnom} = 60 A; V _{GE} = 0 V	T _j = 25 °C _{chiplev.}		1,1	1,6	V		
		T _j = 125 °C _{chiplev.}			1,2	V		
V _{F0}		T _j = 150 °C		0,85		V		
r _F		T _j = 150 °C		12		mΩ		
I _{RRM}	I _F = 40 A	T _i = 125 °C		40		А		
Q _{rr}	di/dt = 1200 A/µs			3		μC		
E _{rr}	V _{CC} =300V			0,42		mJ		
R _{th(j-s)D}	per diode				1,1	K/W		
M _s	to heat sink		2,25		2,5	Nm		
w				30		g		

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

